



BT236X-800G

4Q Triac

1 May 2015

Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT186A "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Isolated package
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

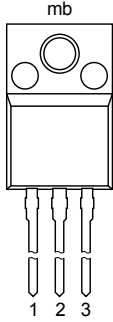

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{J(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	65	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 88\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	6	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	5	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	8	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	11	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	30	100	mA



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220F (SOT186A)</p>	
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT236X-800G	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A
BT236X-800G/L02	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Marking

Table 4. Marking codes

Type number	Marking code
BT236X-800G	BT236X-800G
BT236X-800G/L02	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 88\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	6	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	65	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	21	A^2s
dl_T/dt	rate of rise of on-state current	$I_G = 100\text{ mA}$; T2+ G+	-	50	$A/\mu s$
		$I_G = 100\text{ mA}$; T2+ G-	-	50	$A/\mu s$
		$I_G = 200\text{ mA}$; T2- G+	-	10	$A/\mu s$
		$I_G = 100\text{ mA}$; T2- G-	-	50	$A/\mu s$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}C$
T_j	junction temperature		-	125	$^{\circ}C$

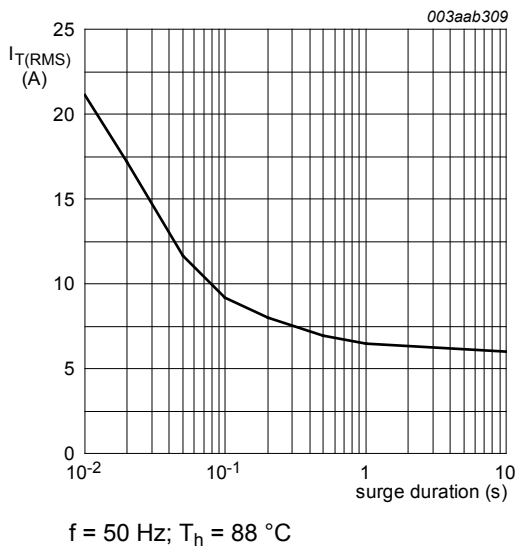


Fig. 1. RMS on-state current as a function of surge duration; maximum values

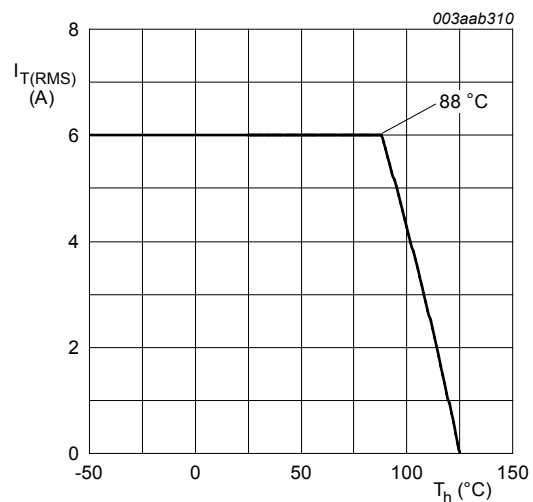


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

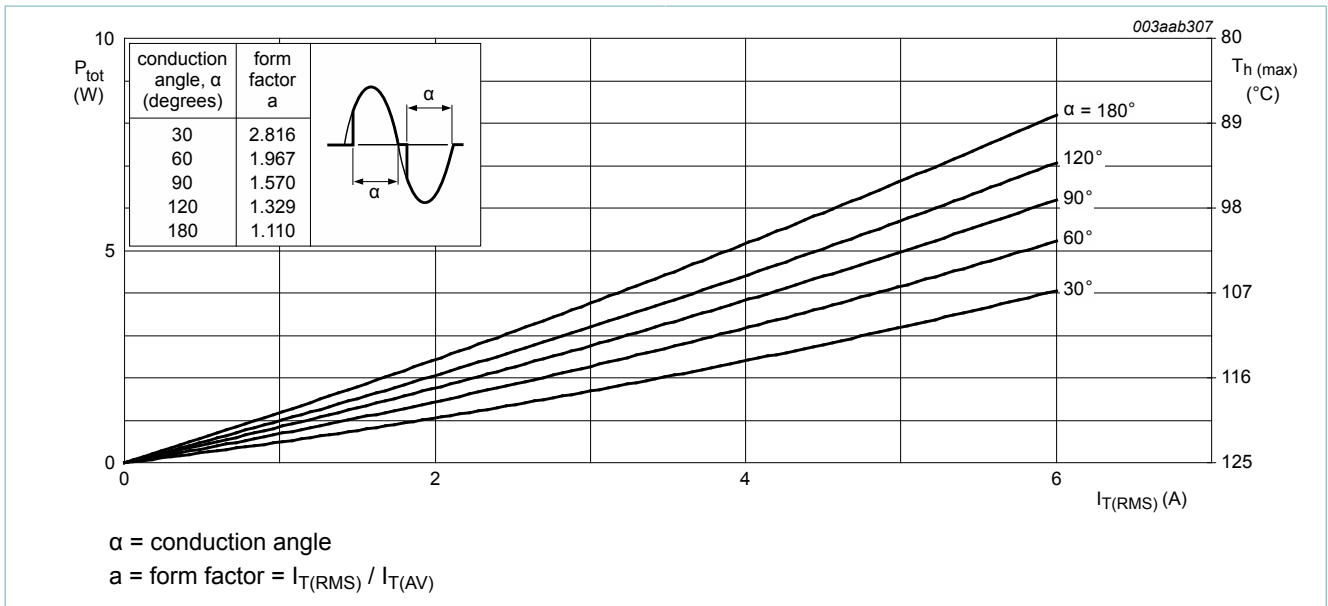


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

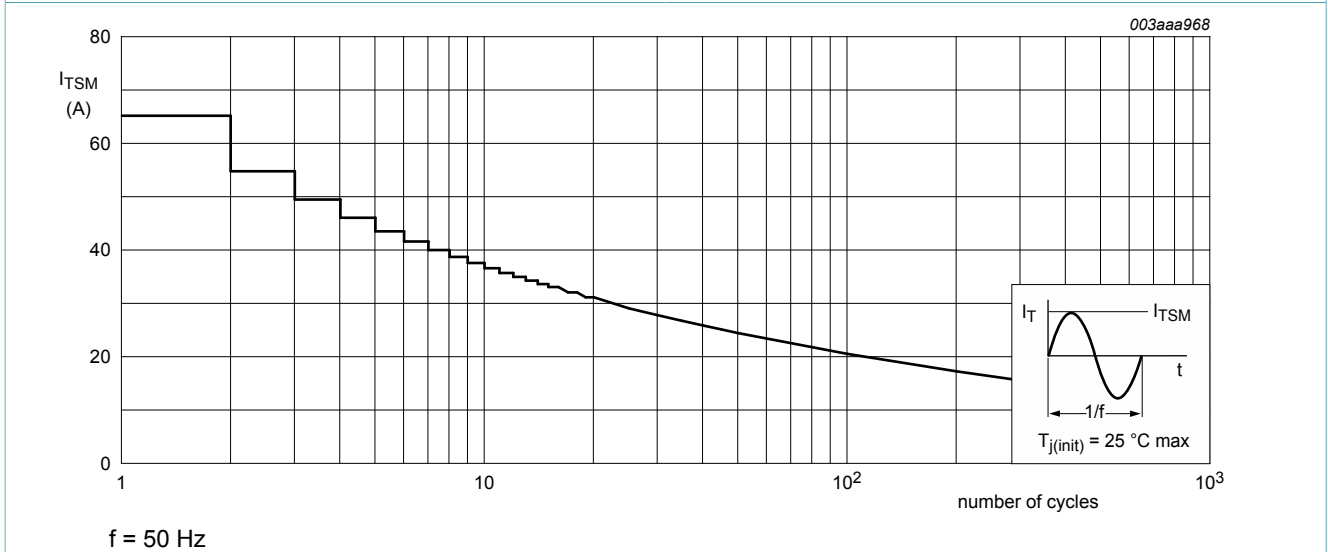


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

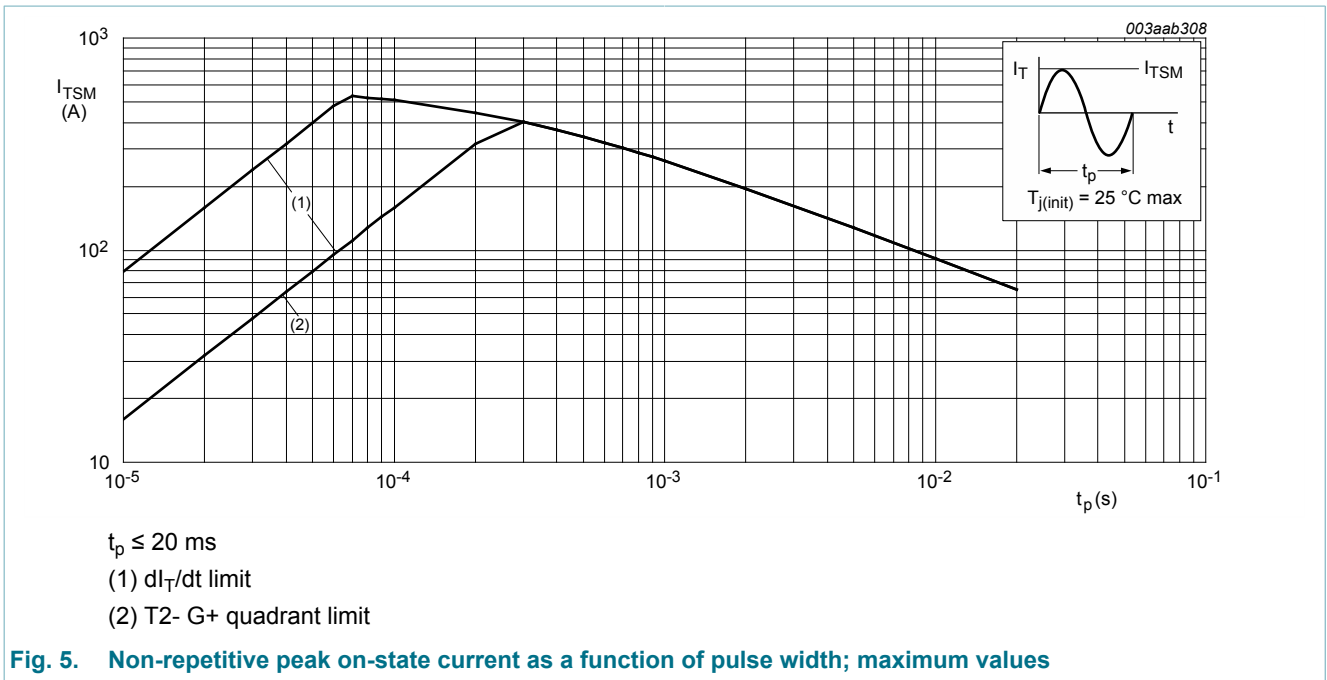
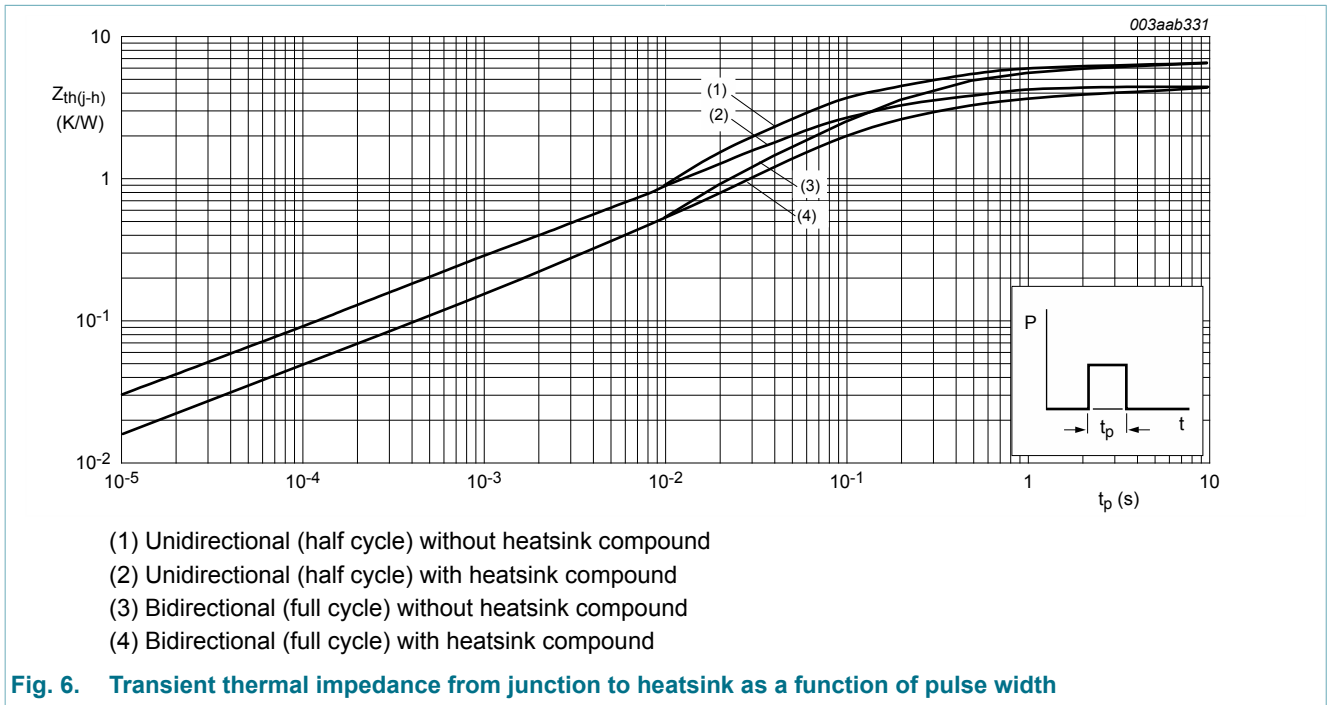


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; without heatsink compound; Fig. 6	-	-	4.5	K/W
		full or half cycle; with heatsink compound; Fig. 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



10. Isolation characteristics

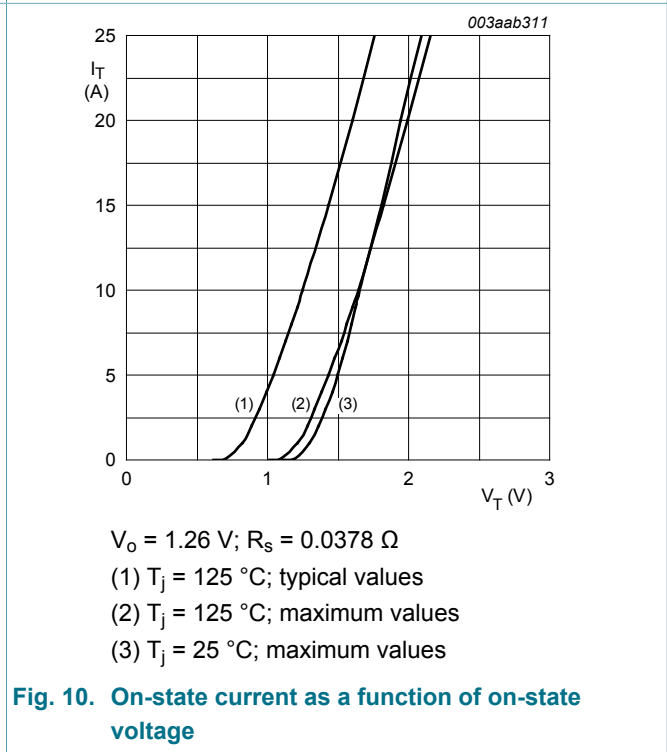
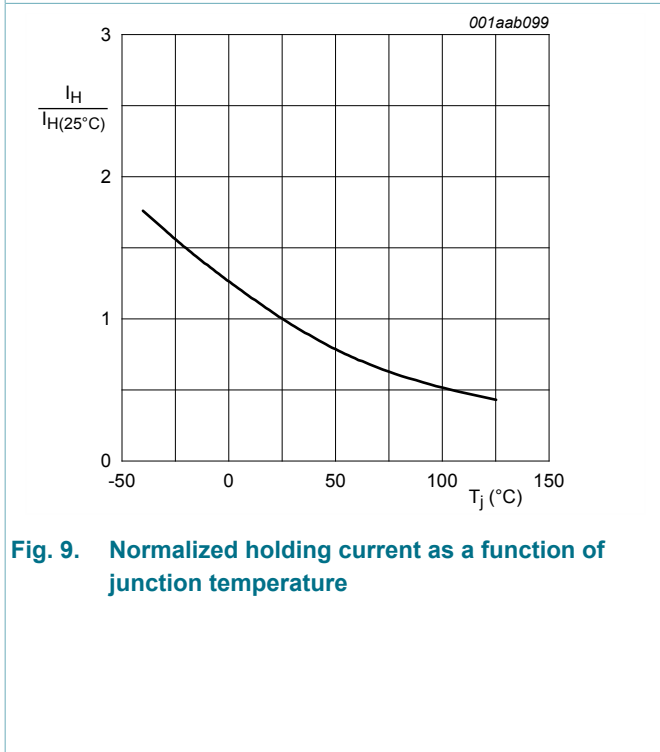
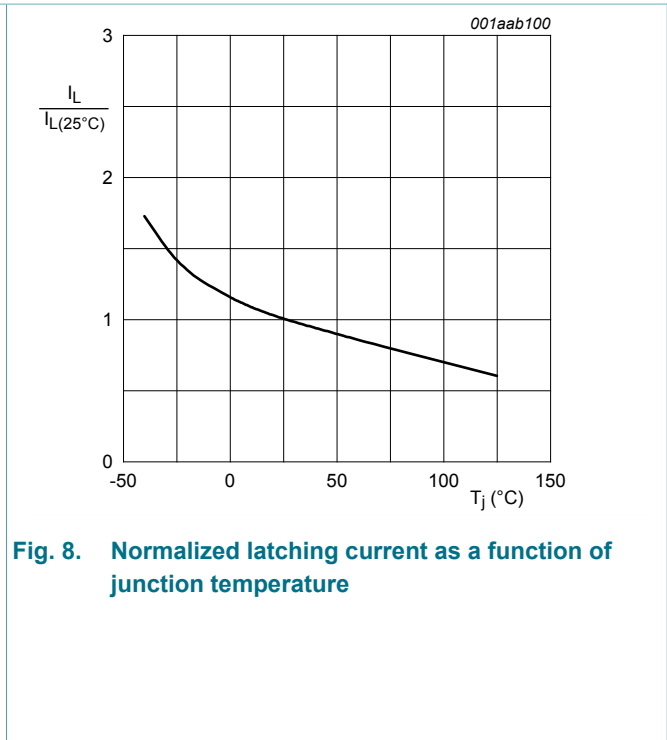
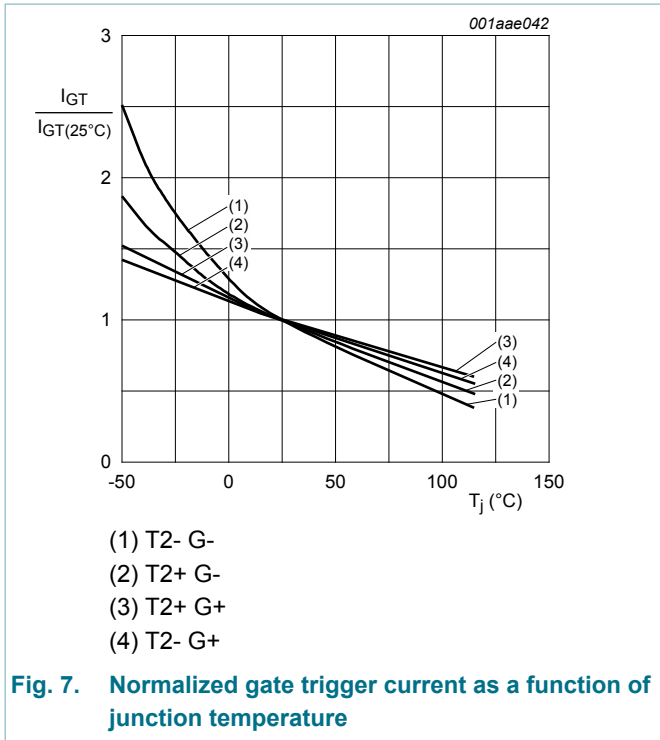
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$; $RH \leq 65\%$; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1\text{ MHz}$; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7	-	5	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	-	8	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7	-	11	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7	-	30	100	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8	-	7	45	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8	-	16	60	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8	-	5	45	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8	-	7	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9	-	5	40	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; Fig. 10	-	1.3	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	200	250	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	V _D = 400 V; T _j = 95 °C; dI _{com} /dt = 3.6 A/ms; I _T = 6 A; gate open circuit	10	20	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 12 A; V _D = 800 V; I _G = 0.1 A; dI _G /dt = 5 A/μs	-	2	-	μs



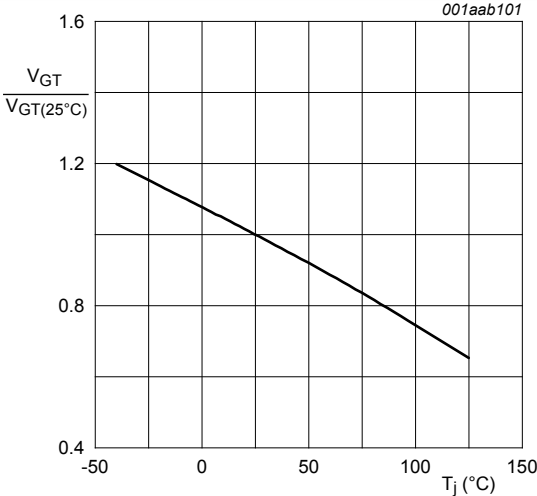


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline



Fig. 12. Package outline TO-220F (SOT186A)

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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